

60V 4.5mohm N-channel SGT MOSFET

AKG6N045GL

Description:

This N channel SGT MOSFET has been designed to very low on-state resistance and maintain superior switching performance, especially for high efficiency power management applications.

Features:

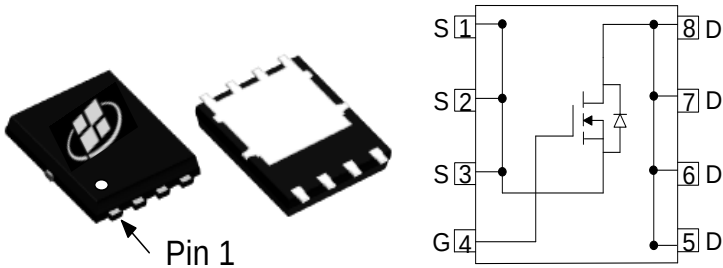
- Low  $R_{DS(ON)}$
- RoHS compliant (Note 1)
- Halogen-free (Note 1)
- 100% UIS Tested

Applications:

- Battery Management System
- Motor Drivers
- DC-DC Converter

Key Performance Parameters:

| Parameter                       | Value | Unit |
|---------------------------------|-------|------|
| $V_{DS}$                        | 60    | V    |
| $R_{DS(ON), max} @V_{GS} = 10V$ | 4.5   | mΩ   |
| $I_D$                           | 80    | A    |



Ordering Information:

| Ordering Code | Package Type | Marking Code | Form      | Packing                            |
|---------------|--------------|--------------|-----------|------------------------------------|
| AKG6N045GL    | PDFN5X6      | G6N045GL     | Tape Reel | See the detail package information |

Notes:

1. Contact ALKAIDSEMI sales for detail information

**Maximum Ratings** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

| Symbol         | Parameter                                                                   | Value       | Units            |
|----------------|-----------------------------------------------------------------------------|-------------|------------------|
| $V_{DS}$       | Drain-Source Voltage                                                        | 60          | V                |
| $I_D$          | Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) <sup>(Note 1)</sup> | 121         | A                |
|                | Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) <sup>(Note 2)</sup> | 80          | A                |
|                | Drain Current - Continuous ( $T_C = 100^\circ\text{C}$ )                    | 77          | A                |
| $I_{DM}$       | Drain Current - Pulsed <sup>(Note 3)</sup>                                  | 320         | A                |
| $V_{GS}$       | Gate-Source Voltage                                                         | $\pm 20$    | V                |
| $E_{AS}$       | Single Pulsed Avalanche Energy <sup>(Note 4)</sup>                          | 210         | mJ               |
| $P_D$          | Power Dissipation ( $T_C = 25^\circ\text{C}$ )                              | 113         | W                |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                     | -55 to +150 | $^\circ\text{C}$ |

**Thermal Characteristics**

| Symbol          | Parameter                                                                 | Value | Units              |
|-----------------|---------------------------------------------------------------------------|-------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Steady-State                        | 1.1   | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient, Steady State <sup>(Note 5)</sup> | 45    | $^\circ\text{C/W}$ |

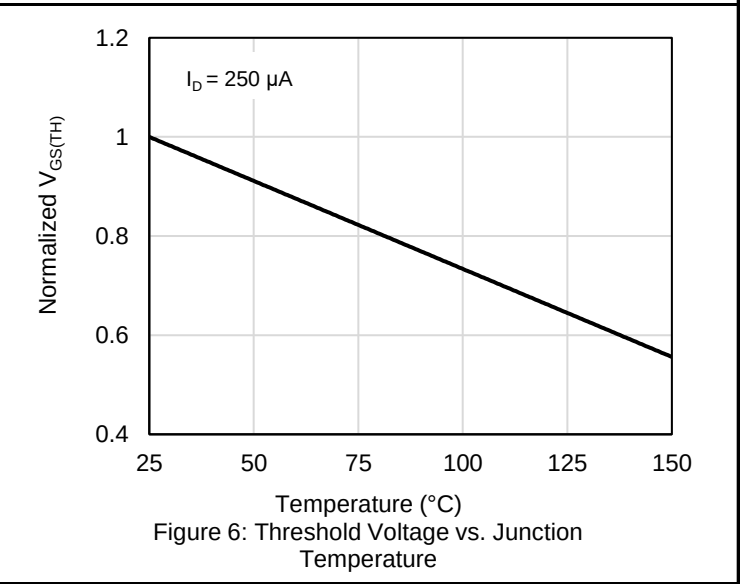
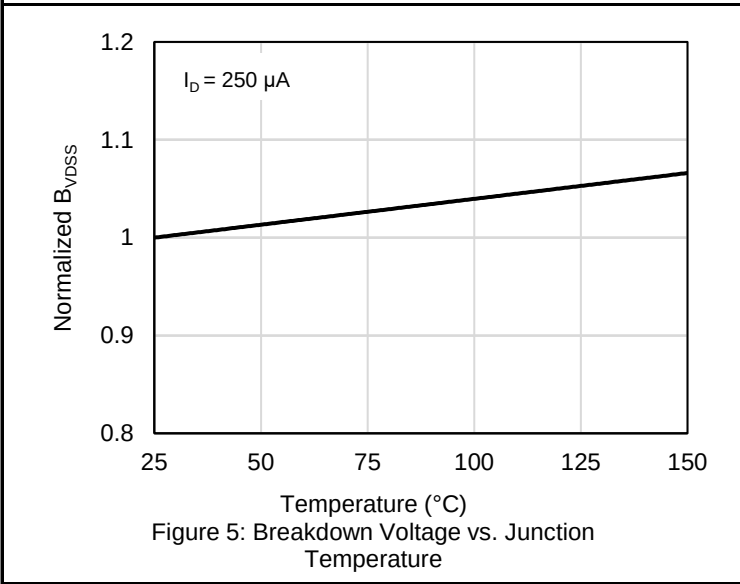
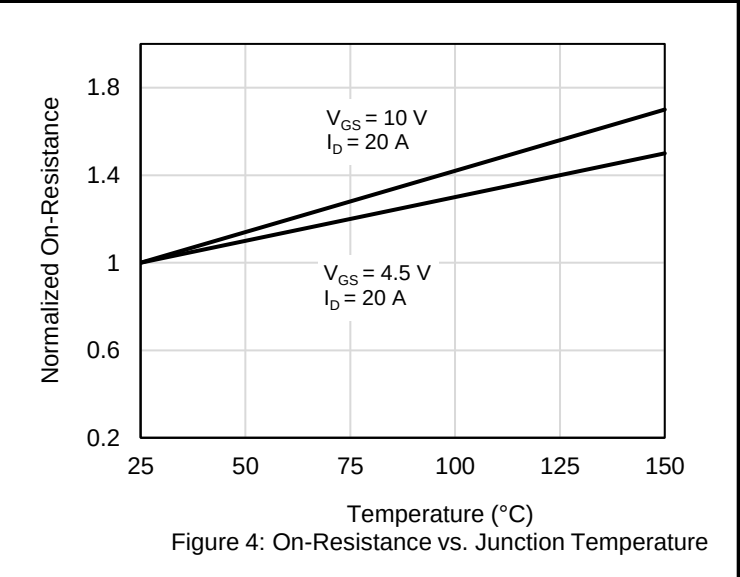
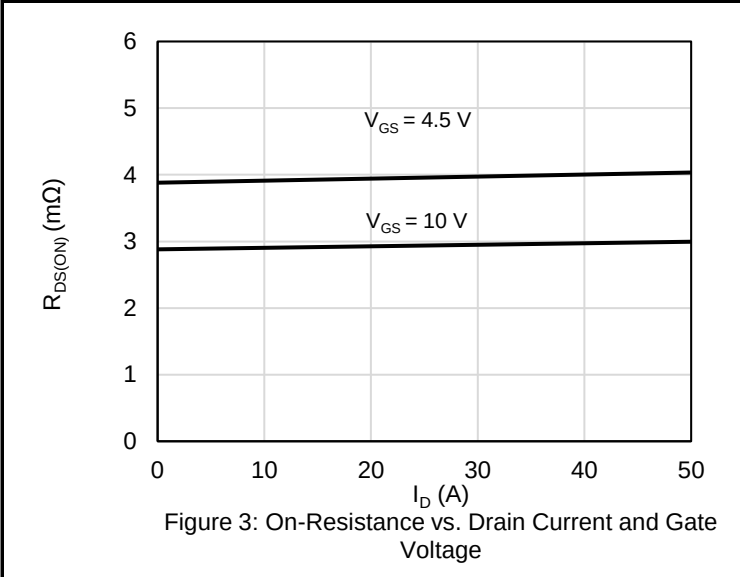
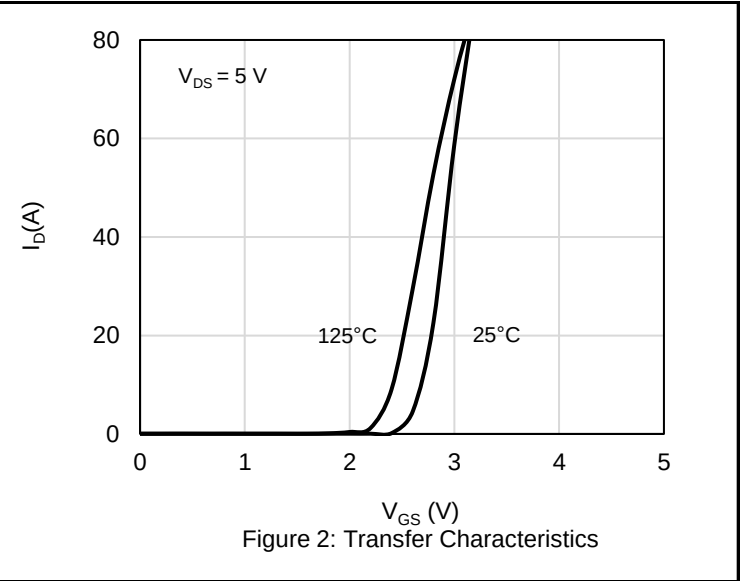
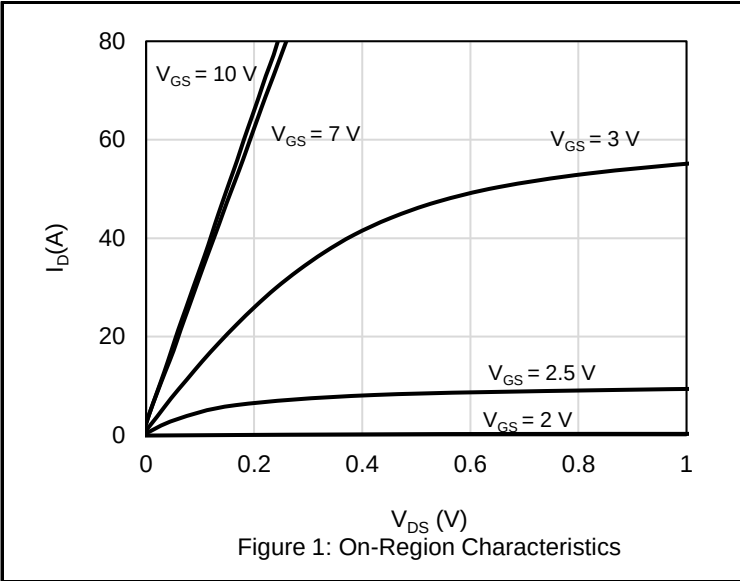
**Notes:**

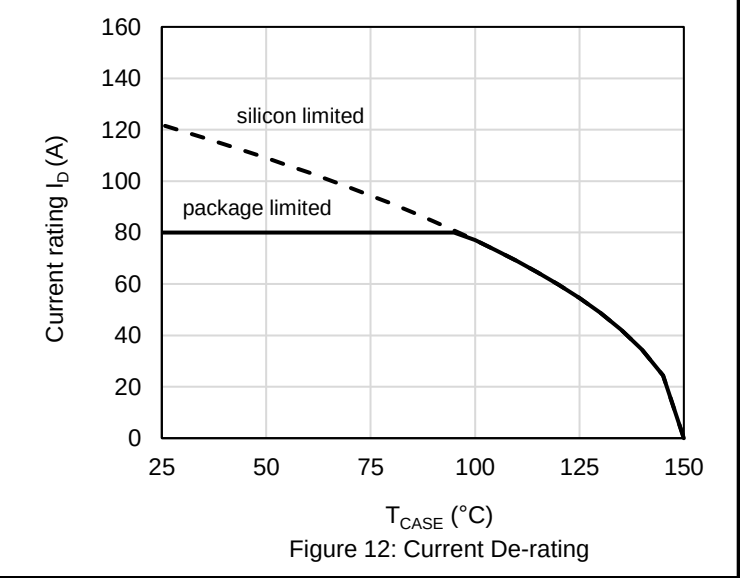
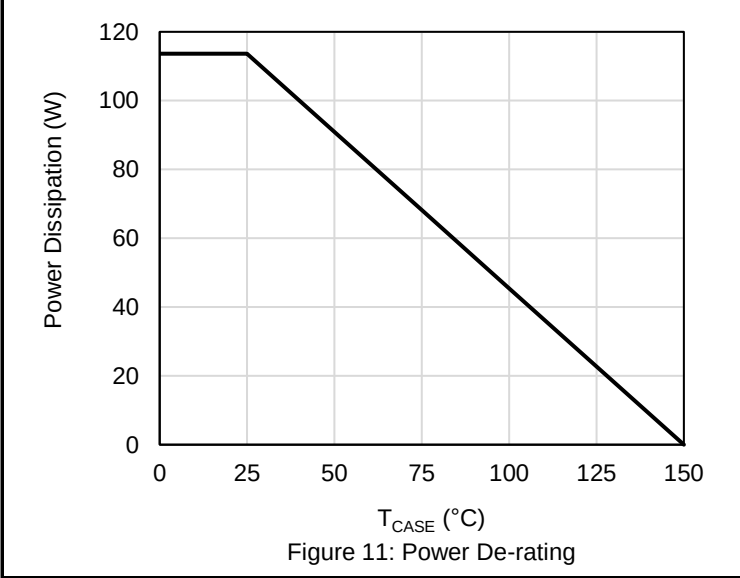
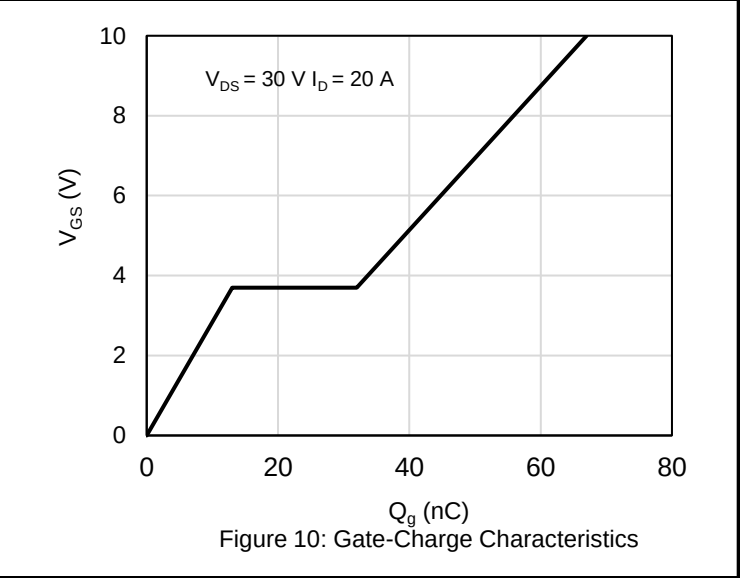
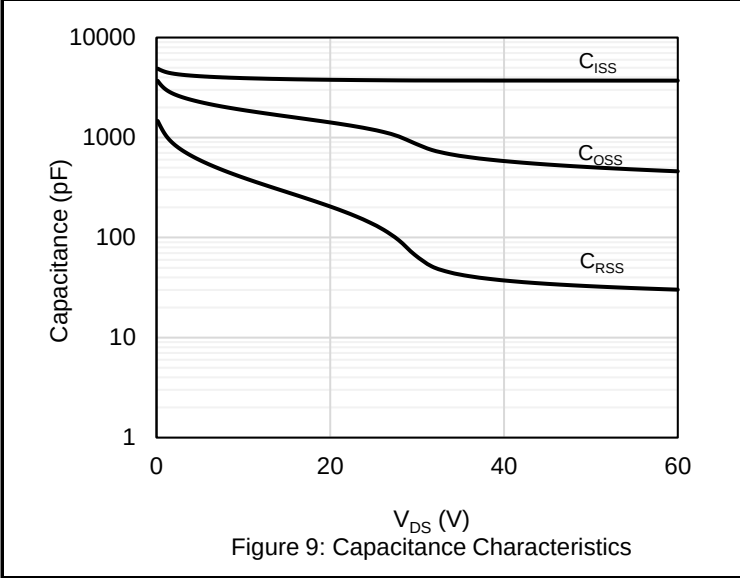
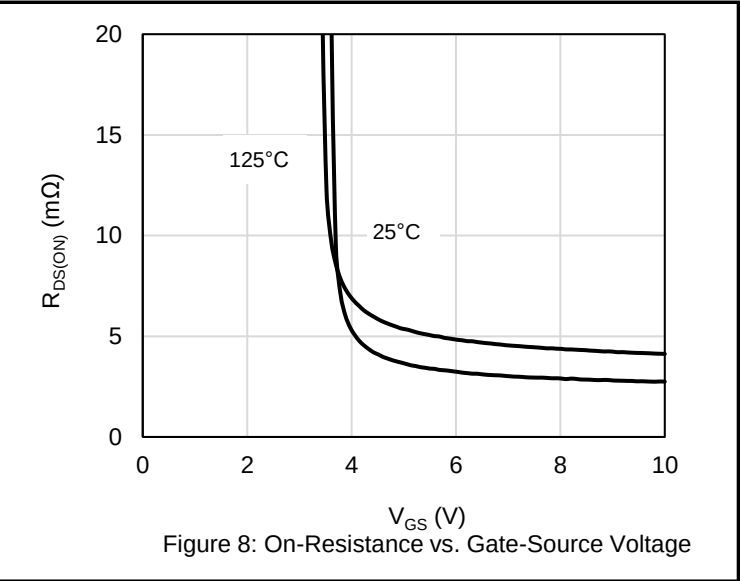
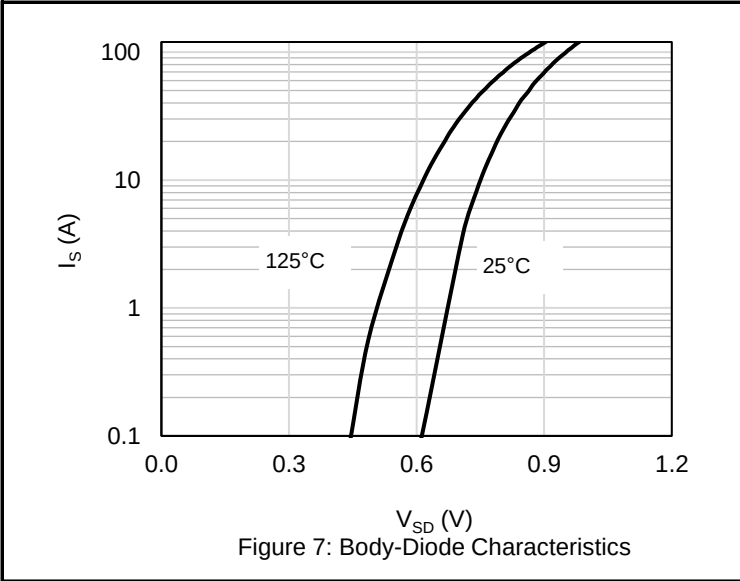
1. The max drain current rating is silicon limited
2. The max drain current rating is package limited
3. Repetitive Rating: Pulse width limited by maximum junction temperature
4.  $L = 0.5\text{ mH}$ ,  $V_{DD} = 30\text{ V}$ ,  $I_{AS} = 29\text{ A}$ ,  $R_G = 25\ \Omega$ , Starting  $T_J = 25\ ^\circ\text{C}$
5. Mount on minimum PCB layout

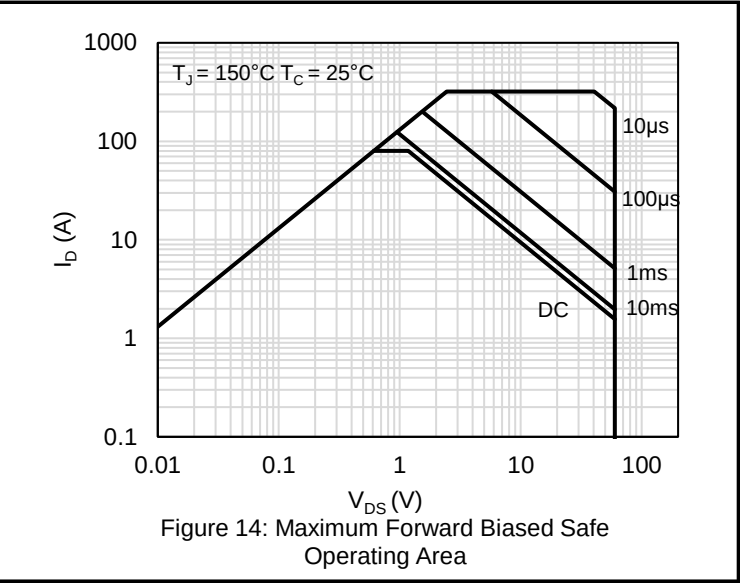
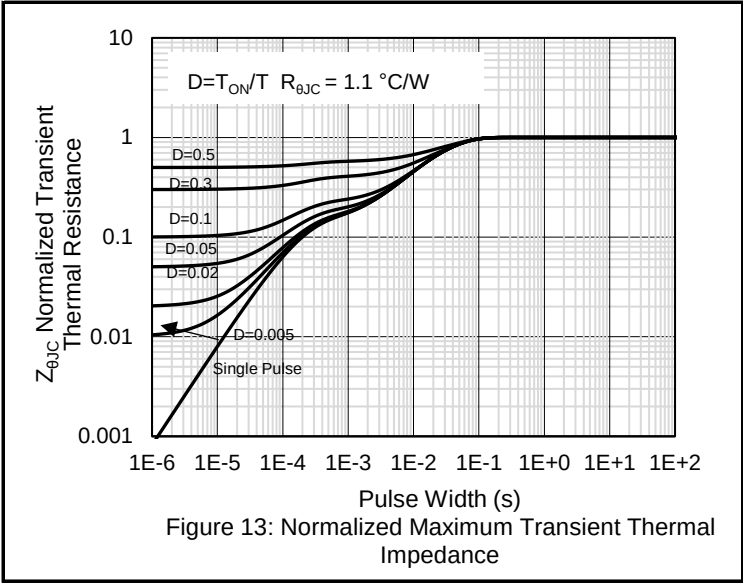
**Electrical Characteristics** ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

| Symbol                                                 | Parameter                                     | Test Conditions                                                                                  | Min | Typ  | Max   | Units |
|--------------------------------------------------------|-----------------------------------------------|--------------------------------------------------------------------------------------------------|-----|------|-------|-------|
| Static Characteristics                                 |                                               |                                                                                                  |     |      |       |       |
| BV <sub>DSS</sub>                                      | Drain-Source Breakdown Voltage                | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                   | 60  |      |       | V     |
| I <sub>DSS</sub>                                       | Zero Gate Voltage Drain Current               | V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V                                                    |     |      | 1     | μA    |
| I <sub>GSS</sub>                                       | Gate Leakage Current                          | V <sub>GS</sub> = ± 20 V, V <sub>DS</sub> = 0 V                                                  |     |      | ± 100 | nA    |
| V <sub>GS(TH)</sub>                                    | Gate Threshold voltage                        | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                      | 1   | 2    | 3     | V     |
| R <sub>DS(ON)</sub>                                    | Drain-Source on-state resistance              | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A                                                    |     | 3    | 4.5   | mΩ    |
|                                                        |                                               | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 20 A                                                   |     | 4    | 6     | mΩ    |
| Dynamic Characteristics                                |                                               |                                                                                                  |     |      |       |       |
| C <sub>ISS</sub>                                       | Input Capacitance                             | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V,<br>F = 1 MHz                                      |     | 3720 |       | pF    |
| C <sub>OSS</sub>                                       | Output Capacitance                            |                                                                                                  |     | 875  |       | pF    |
| C <sub>RSS</sub>                                       | Reverse Transfer Capacitance                  |                                                                                                  |     | 65   |       | pF    |
| R <sub>G</sub>                                         | Gate Resistance                               | F = 1 MHz                                                                                        |     | 1    |       | Ω     |
| Switching Characteristics                              |                                               |                                                                                                  |     |      |       |       |
| T <sub>D(ON)</sub>                                     | Turn On Delay Time                            | V <sub>DD</sub> = 30 V , R <sub>L</sub> = 1.5 Ω,<br>V <sub>GS</sub> = 10 V, R <sub>G</sub> = 6 Ω |     | 15   |       | ns    |
| T <sub>R</sub>                                         | Rise Time                                     |                                                                                                  |     | 42   |       | ns    |
| T <sub>D(OFF)</sub>                                    | Turn Off Delay Time                           |                                                                                                  |     | 67   |       | ns    |
| T <sub>F</sub>                                         | Fall Time                                     |                                                                                                  |     | 48   |       | ns    |
| Q <sub>G</sub>                                         | Total Gate Charge                             | V <sub>DD</sub> = 30 V , I <sub>D</sub> = 20 A,<br>V <sub>GS</sub> = 10 V                        |     | 67   |       | nC    |
| Q <sub>GS</sub>                                        | Gate-Source Charge                            |                                                                                                  |     | 13   |       | nC    |
| Q <sub>GD</sub>                                        | Gate-Drain Charge                             |                                                                                                  |     | 19   |       | nC    |
| Drain-Source Diode Characteristics and Maximum Ratings |                                               |                                                                                                  |     |      |       |       |
| I <sub>S</sub>                                         | Maximum Continuous Body-Diode Forward Current |                                                                                                  |     |      | 80    | A     |
| I <sub>SM</sub>                                        | Maximum Pulsed Body-Diode Forward Current     |                                                                                                  |     |      | 320   | A     |
| V <sub>SD</sub>                                        | Diode Forward Voltage                         | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 20 A                                                     |     | 0.8  |       | V     |
| T <sub>RR</sub>                                        | Reverse recovery time                         | V <sub>DD</sub> = 30 V, I <sub>D</sub> = 20 A,<br>di/dt = 100 A/μs                               |     | 52   |       | ns    |
| Q <sub>RR</sub>                                        | Reverse recovery charge                       |                                                                                                  |     | 66   |       | nC    |
| I <sub>R RM</sub>                                      | Peak Reverse Recovery Current                 |                                                                                                  |     | 2    |       | A     |

Electrical Characteristics Diagrams

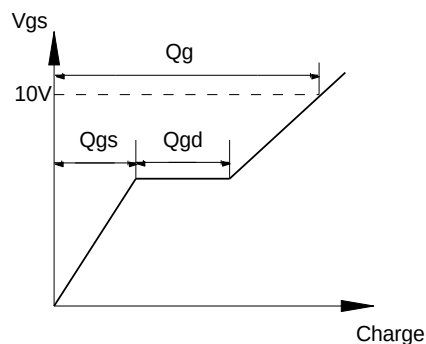
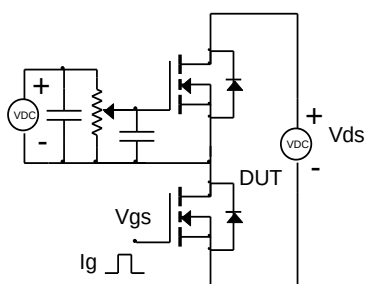




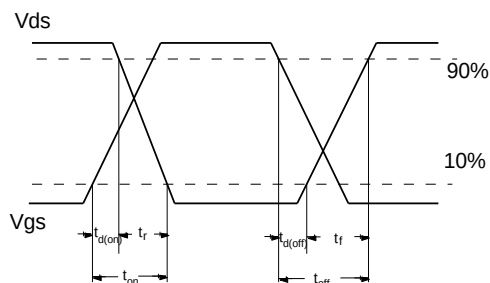
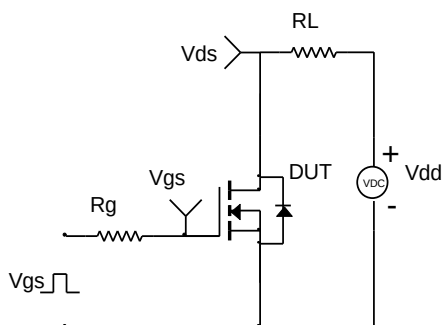


## Test Circuit and Waveform

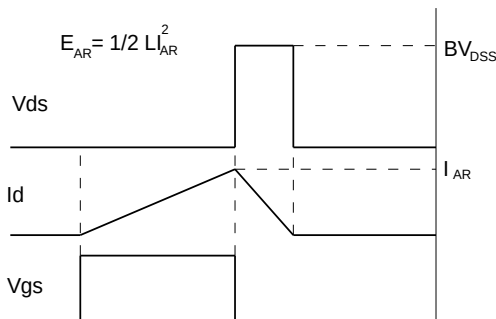
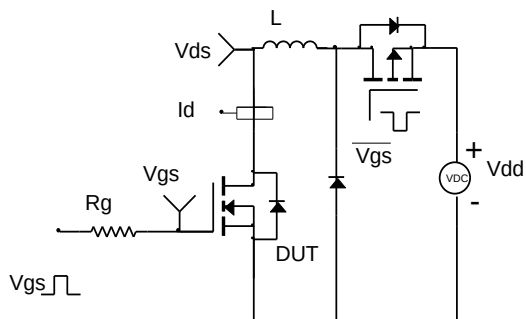
Gate Charge Test Circuit & Waveform



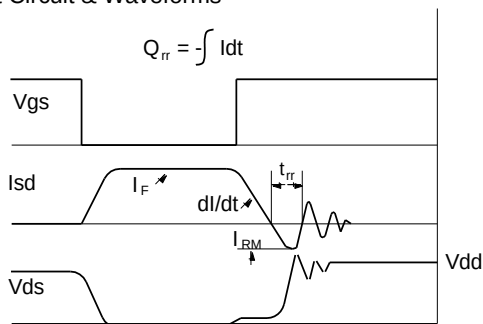
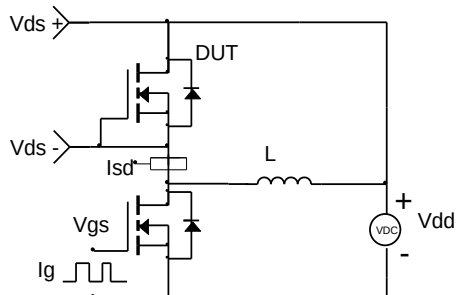
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



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## Revision History

| Revision | Release Date | Remark          |
|----------|--------------|-----------------|
| Rev.1.0  | 2022/7/13    | Initial Release |

## Disclaimer

The information given in this document describes the independent performance of the product, but similar performance is not guaranteed under other working conditions, and cannot be guaranteed when installed with other products or equipment. To achieve the required performance of the product in actual scenarios, the customer should conduct a complete application test to assess the functionality of the product.

Alkaidsemi assumes no responsibility for equipment failures result from using products at values that exceed the ratings, operating conditions, or other parameters listed in the product specifications.

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